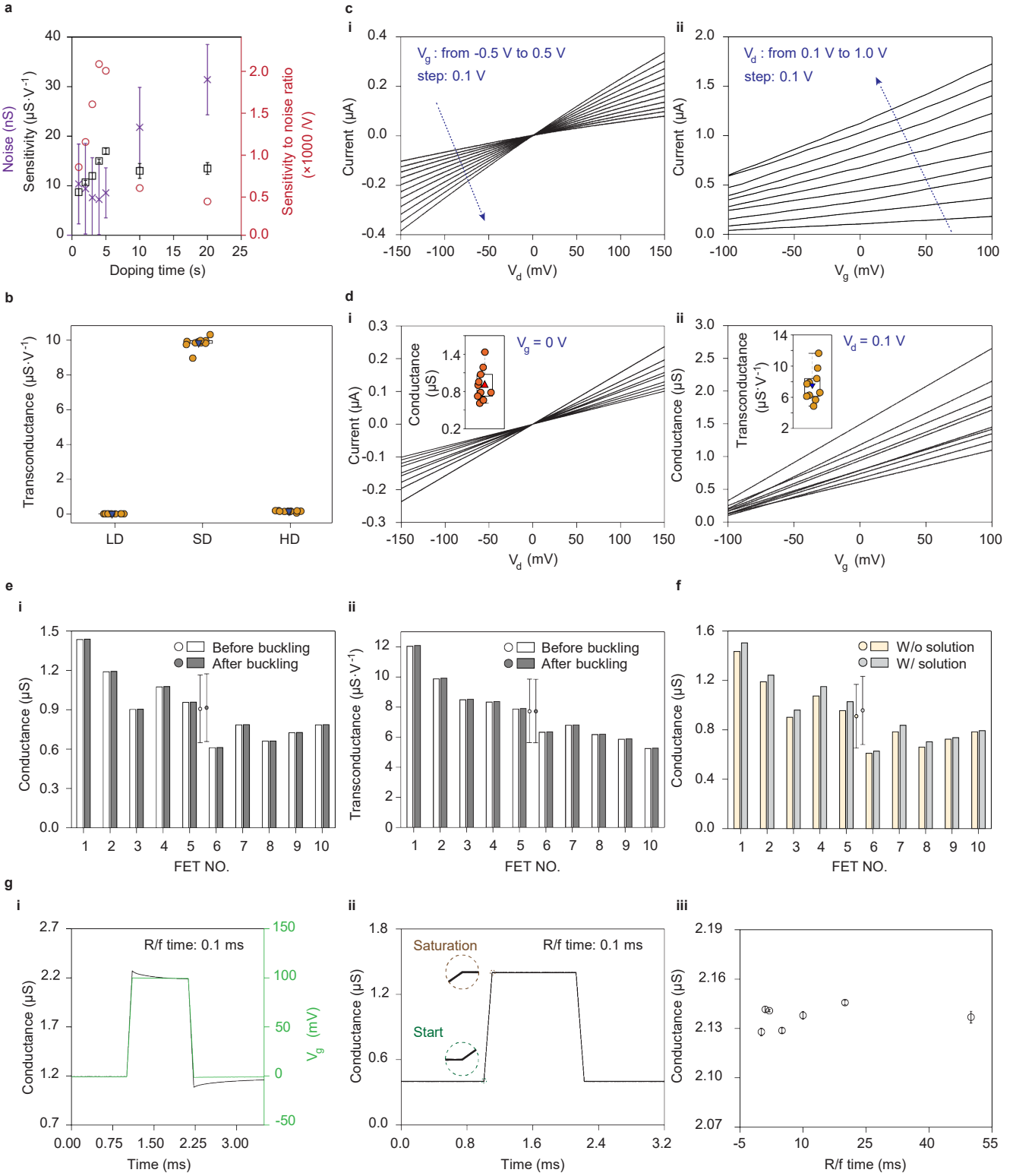
a
Noise (nS)
Sensitivity (μS·V⁻¹)
Sensitivity to noise ratio (×1000 /V)
Doping time (s)
b
Transconductance (μS·V⁻¹)
LD
SD
HD
c
i
V_g : from -0.5 V to 0.5 V
step: 0.1 V
Current (μA)
V_d (mV)
ii
V_d : from 0.1 V to 1.0 V
step: 0.1 V
Current (μA)
V_g (mV)
d
i
V_g = 0 V
Conductance (μS)
Current (μA)
V_d (mV)
ii
V_d = 0.1 V
Transconductance (μS·V⁻¹)
Conductance (μS)
V_g (mV)
e
i
Before buckling
After buckling
Conductance (μS)
FET NO.
ii
Before buckling
After buckling
Transconductance (μS·V⁻¹)
FET NO.
f
W/o solution
W/ solution
Conductance (μS)
FET NO.
g
i
R/f time: 0.1 ms
Conductance (μS)
V_g (mV)
Time (ms)
ii
Saturation
R/f time: 0.1 ms
Start
Conductance (μS)
Time (ms)
iii
Conductance (μS)
R/f time (ms)